(1) Publication number:

0 182 443

**A3** 

(12)

## **EUROPEAN PATENT APPLICATION**

(21) Application number: 85201909.0

(a) Int. Cl.<sup>3</sup>: **G** 03 **B** 41/00 **G** 03 **F** 7/20

(22) Date of filing: 19.11.85

(30) Priority: 21.11.84 US 673964

(43) Date of publication of application: 28.05.86 Bulletin 86/22

(88) Date of deferred publication of search report: 28.10.87

(84) Designated Contracting States: CH DE FR GB IT LI

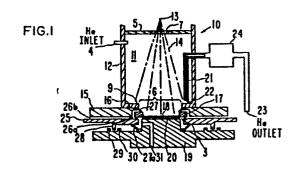
71) Applicant: Micronix Corporation 100 Albright Way Los Gatos California 95030(US)

(72) Inventor: Novak, Thomas W. 15851 Miradero Drive San Jose California 95127(US)

(4) Representative: Noz, Franciscus Xaverius, Ir. et al, Boschdiik 155 NL-5612 HB Eindhoven(NL)

(S) X-ray lithographic system, in particular gas control for the same, and method for fabricating a semiconductor substrate.

(57) An X-ray lithographic system and method for beam printing on a substrate such as a silicon semiconductor wafer includes a beam exposure chamber (11), a beam source (13), a mask holder (15), a mask (17) including a thin mask membrane (18) closing the exit end (6) of the chamber. A controlled flow of low X-ray attenuating gas such as helium is provided to an upper remote portion of the exposure chamber and vent means (21) extends from a lower portion of the chamber adjacent the mask to an exterior exit orifice (23) positioned at mask level to prevent ingress of air to the chamber and prevent deflection and change in the mask-tosubstrate gap distance. The substrate (20) is positioned below the mask membrane and is surrounded by a mask-towafer zone into which is flowed a substrate fabrication process gas which is vented either by a gas flange (25) in spaced gapped relation to the mask holder and mask, or by a vent tube (46) extending from said zone to an orifice end (46a) approximate the level of said mask to assure no pressure differential on the top and bottom surfaces of the mask membrane affecting the mask-to-wafer gap distance (8) during substrate fabrication operations.



0



## **EUROPEAN SEARCH REPORT**

Application number

EP 85 20 1909

Sategory	Citation of document with indication, where appropriate, of relevant passages			levant claim			
			<del>-   "</del>		<u> </u>		or (nit. Ot)
x	WO-A-7 900 340 ELECTRIC) * Whole document		1,	2			41/00 7/20
E	EP-A-O 178 660 * Whole document		1,	2			
A	EP-A-0 110 414 * Pages 2,3 *	- (HITACHI)	1				
		<b></b>			-		
							AL FIELDS D (Int. Ci 4)
						03 B 03 F	
	The present search report has b	een drawn up for all claims					
Place of search THE HAGUE		Date of completion of the search 21-08-1987		Examiner SEIFERT			
đ	CATEGORY OF CITED DOCL articularly relevant if taken alone articularly relevant if combined w ocument of the same category schnological background ion-written disclosure	E : earlier :	e filino da	te			ion on, or